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Small and Medium Diodes



Small and Medium Diodes

Recently, many products ranging from computers and home appliances to automobiles and industrial equipment have been driving the need for effective solutions to reduce size and weight. Semiconductor requirements differ from application to application. Take power supplies for example, which are being required to accommodate higher capacity in smaller dimensions. This increases the temperature at which systems are operated.

To meet these requirements, Toshiba offers an extensive portfolio of small, high-efficiency diodes, including Schottky barrier diodes (SBDs) featuring high-speed operation and low forward loss.

Diodes

Schottky Barrier Diodes (SBDs)

Toshiba offers low-loss SBDs fabricated with a next-generation process. These SBDs will help increase the performance of equipment that requires a small form factor and high efficiency, such as mobile devices and switching power supplies. SBDs with a reverse voltage of 20 V to 60 V and an average forward current of 0.7 A to 5 A are available in small surface-mount packages. You will find SBDs that best suit your applications.

Rectifier Diodes

General-Purpose Rectifiers and reverse-current protection

Super-Fast-Recovery Diodes (S-FRDs)

High-Efficiency Diodes (HEDs)

Diodes with a reverse voltage of 200 V to 1000 V and an average forward current of 0.5 A to 3 A are available in small surface-mount packages. Toshiba's product portfolio also includes diodes with high ESD performance ideal for automotive applications.

Zener Diodes

Zener diodes are available with a wide range of Zener voltage specifications from 6.2 V to 82 V. They can be used for a wide range of applications such as consumer, automotive and industrial electronics.

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•	[Product Lineup]10
	Device Marking

This brochure contains information on small and medium diodes only. For switching diodes, small-signal Schottky barrier diodes and ESD protection diodes, see the following brochure or our homepage:

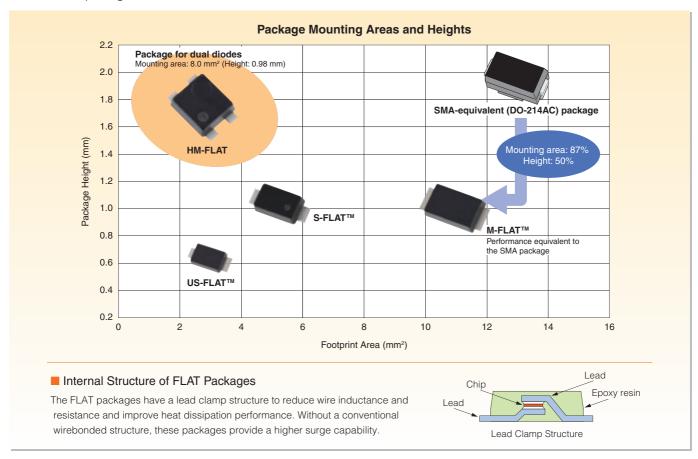
- ◆ Homepage http://toshiba.semicon-storage.com/
- ◆ Brochure Discrete Semiconductors, Linear ICs, Logic ICs

Product Lineup

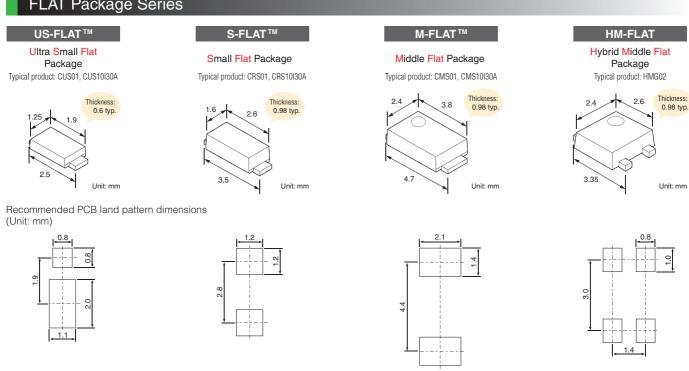
SMALL & MEDIUM DIODES

Surface-Mount Package Trend for Diodes

In order to help improve the performance of information and communications equipment, Toshiba offers high-efficiency diodes in small surface-mount packages.



FLAT Package Series



Note: The PCB land pattern dimensions shown above are for reference only and should be determined empirically.

Schottky Barrier Diodes (SBDs)

SMALL & MEDIUM DIODES

Schottky barrier diodes (SBDs) have a junction formed between a semiconductor and a metal such as molybdenum, instead of a PN junction. Unlike PN junction diodes, SBDs are majority carrier devices. Therefore, SBDs feature low forward voltage and short reverse recovery time, making them ideal for high-speed switching applications.

Toshiba offers SBDs fabricated using a new process that provides an improved VF-IRRM trade-off. These new SBDs, together with conventional SBDs, will meet diverse design requirements.

Schottky-Barrier Diodes (SBDs) with Improved Trade-Off

Toshiba now offers small to medium SBDs fabricated with a new process. Owing to low peak forward voltage (VFM) and low repetitive peak reverse current (IRRM) characteristics, these SBDs provide low power loss and thus help reduce the size and improve the power efficiency of mobile handsets, switching power supplies, etc.

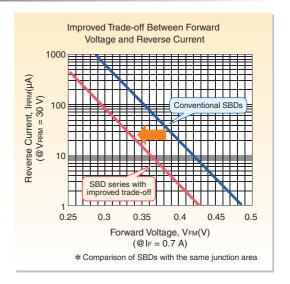
Voltage rating: VRRM = 30 V, 40 VCurrent rating: IF(AV) = 1 A to 3 A

► Peak forward voltage (Typical characteristics: CRS10I30A)

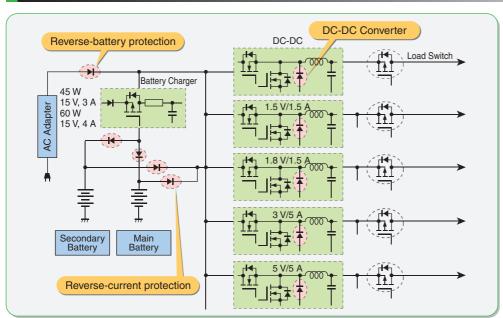
 $V_{FM} = 0.35 V \text{ typ.}$

0.39 V max (@IFM = 0.7 A)

► Small surface-mount packages (US-FLAT™/S-FLAT™/M-FLAT™)



Application Example: Notebook PC





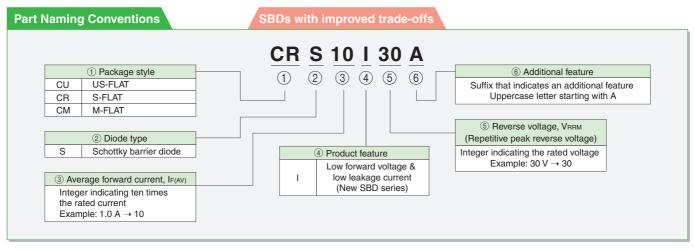
Applications	Package	Recommended Diodes
Daviere a bettern and	US-FLAT™	CUS01, CUS02, CUS10I30A, CUS15I30A
Reverse-battery and reverse-current protection	S-FLAT™	CRS01, CRS03, CRS05, CRS06, CRS08, CRS09, CRS11, CRS14
reverse-current protection	M-FLAT™	CMS01, CMS03, CMS06, CMS07, CMS08, CMS09, CMS16
DC-DC converters	S-FLAT™	CRS03, CRS04, CRS05, CRS09, CRS13, CRS10I30A, CRS15I30A, CRS20I30A
DC-DC converters	M-FLAT™	CMS03, CMS05, CMS14, CMS15, CMS20I30A, CMS30I30A, CMS20I40A, CMS30I40A

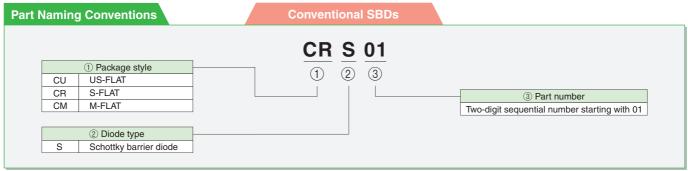
Product Selection Guide

See page 10 for electrical specifications.

Average Forward	Package		Repetitive Peak Re	everse Voltage, VRRM	
Current, IF(AV)	Fackage	20 V	30 V	40 V	60 V
0.7 A	US-FLAT™			CUS03	CUS04
	US-FLAT™	CUS05 CUS06	CUS01 CUS02 CUS10I30A	CUS10I40A	
1 A	S-FLAT™	CRS06	CRS01 CRS03 CRS05 CRS11 CRS10130A CRS10130B CRS10130C	CRS04 CRS10I40A CRS10I40B	CRS12 CRS13
	M-FLAT™		CMS08 CMS09 CMS10I30A	CMS10 CMS10I40A	
	US-FLAT™		CUS15I30A		
1.5 A	S-FLAT™		CRS08 CRS09 CRS15I30A CRS15I30B	CRS15I40A	
	M-FLAT™			CMS15I40A	
	S-FLAT™		CRS14 CRS20I30A CRS20I30B	CRS20I40A CRS20I40B	
2 A	M-FLAT™		CMS06 CMS07 CMS17 CMS20I30A	CMS11 CMS20I40A	CMS14
	S-FLAT™		CRS15♦ CRS30I30A		
3 A	M-FLAT™		CMS01 CMS03 CMS30I30A	CMS16 CMS30I40A	CMS15
5 A	M-FLAT™		CMS04 CMS05		

♦: IF(DC) = 3 A





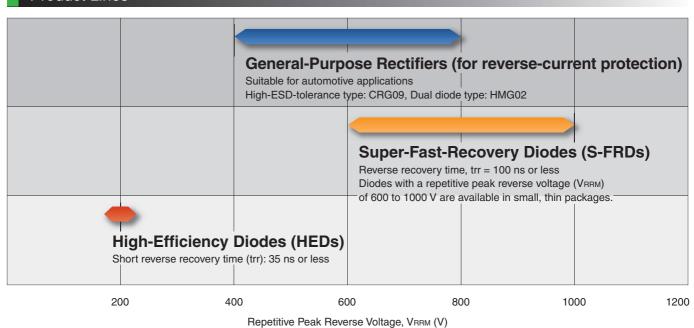
Rectification Diodes

► SMALL & MEDIUM DIODES

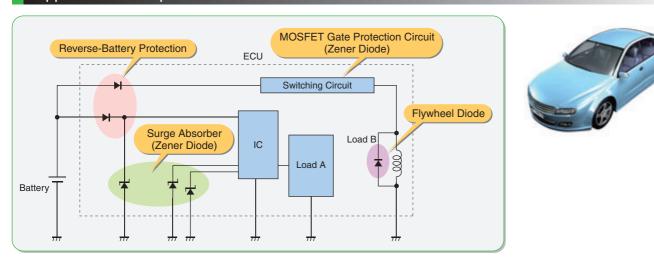
Toshiba offers rectification diodes in surface-mount packages with a reverse voltage ranging from 200 V to 1000 V and an average forward current ranging from 0.5 A to 3 A.

Toshiba's product portfolio of General-Purpose Rectifiers (for reverse-current protection) includes diodes with high ESD tolerance and dual diode devices suitable for automotive applications. Super-Fast Recovery Diodes (S-FRDs) are available in small, thin packages with a VRRM of up to 1000 V. High-Efficiency Diodes (HEDs) provide a short reverse recovery time of 35 ns or less.

Product Lines



Application Example: Automobiles



Applications	Package	Recommended Diodes
Reverse-battery and	S-FLAT™	CRG04, CRG05, CRG07, CRG09, CRG03, HMG02
reverse-current protection	M-FLAT™	CMG02, CMG03, CMG05, CMG06, CMG07, CMG08
Flywbooling	S-FLAT™	CRH01, CRH02
Flywheeling	M-FLAT™	CMH01, CMH04, CMH07

^{*} See "Zener Diodes" on pages 8-9 for a description of diodes for MOSFET gate protection and surge absorber applications.

Product Selection Guide

► General-Purpose Rectifiers (for reverse-current protection)

See page 11 for electrical specifications.

Average Forward	Package -	Repetitive Peak Reverse Voltage, VRRM						
Current, IF(AV)		400 V	600 V	800 V				
0.7.4	HM-FLAT	HMG02 (1)						
0.7 A	S-FLAT™	CRG07						
	S-FLAT™	CRG03	CRG04	CRG05				
		CRG09 (2)						
1 A		CMC02 (3)	CMG06					
	M-FLAT™	CMG05	CMG08					
		CMG07						
2 A	M-FLAT™	CMG02	CMG03					

- (1) Dual diodes (two separate diodes)
- (2) High ESD protection(3) Designed for strobe discharge applications.

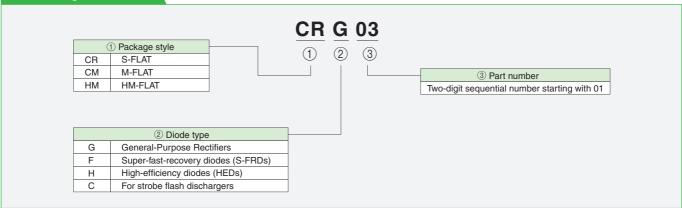
► Super-Fast-Recovery Diodes (S-FRDs)

Average Forward	Dookogo	Reverse Recovery	Repetitive Peak Reverse Voltage, VRRM						
Current, I _{F(AV)}	Package	Time, trr (Max)	600 V	800 V	900 V	1000 V			
0.5.4	S-FLAT™			CRF02					
0.5 A	M-FLAT™			CMF04	CMF03	CMF05			
0.7 A	S-FLAT™	100 ns	CRF03						
1 A	M-FLAT™		CMF02						
2 A	M-FLAT™		CMF01						

► High-Efficiency Diodes (HEDs)

Average Forward Current, IF(AV)	Package	Reverse Recovery Time, t _{rr} (Max)	Repetitive Peak Reverse Voltage, VRRM 200 V
0.5 A	S-FLAT™	35 ns	CRH02
4 A	S-FLAT™		CRH01
1 A	M-FLAT™		CMH04
2 A	M-FLAT™		CMH07
3 A	M-FLAT™		CMH01

Part Naming Conventions



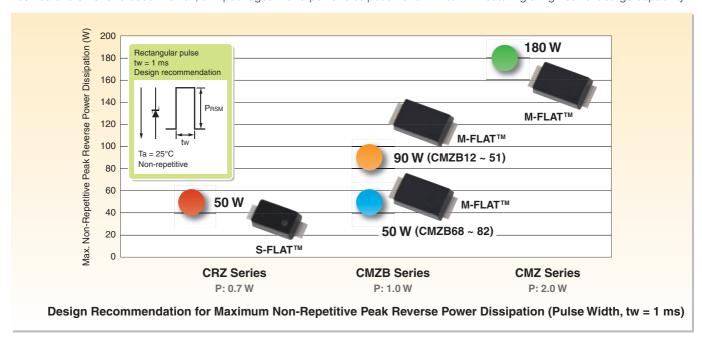
Zener Diodes

SMALL & MEDIUM DIODES

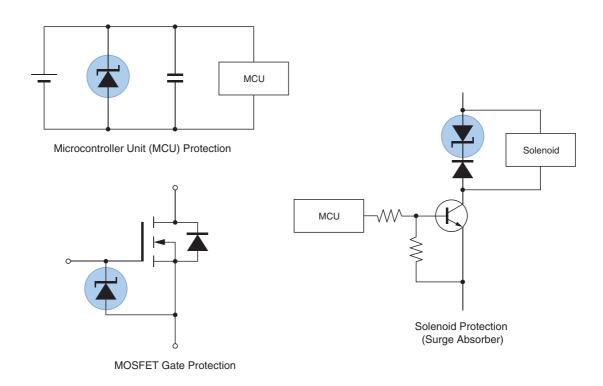
Recent electronic circuits generally incorporate microcontrollers and memory chips to provide complicated control functions. High-precision voltage regulation is required to drive these advanced devices. To address this need, Toshiba offers Zener diodes for constant-voltage regulation for a wide range of input voltage from 6.2 V to 82 V. Zener diodes can also be used for circuit protection purposes such as surge absorption and noise limiting. They are suitable for a broad spectrum of applications, including commercial, automotive and industrial equipment.

Features

Toshiba offers Zener diodes in small, thin packages with a power dissipation of 0.7 W to 2 W featuring a high current surge capability.



Basic Circuit Example

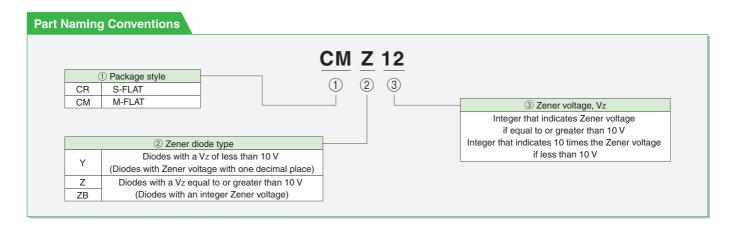


Product Selection Guide

See pages 12-13 for electrical specifications.

Power Dissipation	0.7 W	1.0 W	2.0 W		
Zener Voltage Package Vz(V) typ.	S-FLAT™	M-FLAT™			
6.2	CRY62				
6.8	CRY68				
8.2	CRY82				
10	CRZ10				
12	CRZ12	CMZB12	CMZ12		
13	CRZ13	CMZB13	CMZ13		
15	CRZ15	CMZB15	CMZ15		
16	CRZ16				
18	CRZ18	CMZB18	CMZ18		
20	CRZ20	CMZB20	CMZ20		
24	CRZ24	CMZB24	CMZ24		
27	CRZ27	CMZB27	CMZ27		
30	CRZ30	CMZB30	CMZ30		
33	CRZ33	CMZB33	CMZ33		
36	CRZ36	CMZB36	CMZ36		
39	CRZ39	CMZB39	CMZ39		
43		CMZB43	CMZ43		
47		CMZB47	CMZ47		
51		CMZB51	CMZ51		
68		CMZB68			
75		CMZB75			
82		CMZB82			

The Zener voltage values listed above are the values measured at the specified Zener current (Iz). For Zener voltage measurement, a pulse measurement method is used to minimize the increase in diode temperature. Therefore, Zener voltage could be different, depending on the actual usage conditions and Zener current. Temperature changes and variations should also be considered. When Zener voltage starts to rise (i.e., while Zener current is still low), a Zener diode has a large dynamic resistance (rd), causing significant variations in Zener voltage. For voltage regulation purposes, it is desirable to use a Zener diode in a low dynamic resistance region where sufficient Zener current flows.



Product Characteristics

SMALL & MEDIUM DIODES

Schottky Barrier Diodes (SBDs)

											(Ta = 25°C)
Package	Part Number		Absolute	e Maximu	m Ratings	5		Electri	ical Charad	cteristics (M	lax)
rackage	Fait Number	VRRM (V)	IF(AV) (A)	IFSM (A)	T _j (°C)	T _{stg} (°C)	IRRM (mA)	VFM (V)	@ IFM (A)	C _j (pF) typ.	Conditions
	CUS05	20	1.0	20	125	-40 to 150	1.0	0.37	0.7	40	
	CUS06	20	1.0	20	150	-40 to 150	0.03	0.45	0.7	40	
	CUS01	30	1.0	20	125	-40 to 150	1.5	0.37	0.7	40	
	CUS02	30	1.0	20	150	-40 to 150	0.1	0.45	0.7	40	\/- 10\/
200	CUS10I30A	30	1.0	20	150	-55 to 150	0.06	0.39	0.7	50	VR = 10 V, f = 1 MHz
	CUS15I30A	30	1.5	20	150	-55 to 150	0.06	0.46	1.5	50	1 – 1 1011 12
US-FLAT™	CUS03	40	0.7	20	150	-40 to 150	0.1	0.52	0.7	45	
	CUS10I40A	40	1.0	20	150	-55 to 150	0.06	0.49	0.7	35	
	CUS04	60	0.7	20	150	-40 to 150	0.1	0.58	0.7	38	
	CRS06	20	1.0	20	125	-40 to 150	1	0.36	1.0	60	
	CRS01	30	1.0	20	125	-40 to 150	1.5	0.37	0.7	40	
	CRS03	30	1.0	20	150	-40 to 150	0.1	0.45	0.7	40	
	CRS05	30	1.0	20	150	-40 to 150	∇	0.45	1.0	60	
	CRS11	30	1.0	20	125	-40 to 150	1.5	0.36	1.0	60	
	CRS10I30A	30	1.0	20	150	-55 to 150	0.06	0.39	0.7	50	
	CRS10I30B	30	1.0	20	150	-55 to 150	0.06	0.42	1.0	50	
	CRS10I30C	30	1.0	30	150	-55 to 150	0.1	0.36	1.0	82	
	CRS08	30	1.5	30	125	-40 to 150	1	0.36	1.5	90	
	CRS09	30	1.5	30	150	-40 to 150	0.05	0.46	1.5	90	
	CRS15I30A	30	1.5	20	150	-55 to 150	0.06	0.46	1.5	50	
2.0	CRS15I30B	30	1.5	30	150	-55 to 150	0.1	0.40	1.5	82	VR = 10 V,
_	CRS14	30	2.0	30	150	-40 to 150	0.05	0.49	2.0	90	f = 1 MHz
S-FLAT™	CRS20I30A	30	2.0	20	150	-55 to 150	0.06	0.49	2.0	50	
O I EAI	CRS20I30B	30	2.0	30	150	-55 to 150	0.1	0.45	2.0	82	
	CRS15♦	30	3.0	30	150	-40 to 150	0.05	0.52	3.0	90	
	CRS30I30A	30	3.0	30	150	-55 to 150	0.1	0.49	3.0	82	
	CRS04	40	1.0	20	150	-40 to 150	0.1	0.49	0.7	47	
	CRS10I40A	40	1.0	20	150	-55 to 150	0.06	0.49	0.7	35	
	CRS10I40B	40	1.0	25	150	-55 to 150	0.1	0.45	1.0	62	
	CRS15I40A	40	1.5	20	150	-55 to 150	0.06	0.55	1.5	35	
	CRS20I40A	40	2.0	20	150	-55 to 150	0.06	0.60	2.0	35	
	CRS20I40B	40	2.0	25	150	-55 to 150	0.1	0.52	2.0	62	
	CRS12	60	1.0	20	150	-55 to 150	0.1	0.58	1.0	40	
	CRS13	60	1.0	20	150	-55 to 150	0.05	0.55	1.0	40	
	CMS08	30	1.0	25	125	-40 to 150	1.5	0.37	1.0	70	
	CMS09	30	1.0	25	150	-40 to 150	0.5	0.45	1.0	70	
	CMS10I30A	30	1.0	30	150	-55 to 150	0.1	0.36	1.0	82	
	CMS06	30	2.0	40	125	-40 to 150	3.0	0.37	2.0	130	
	CMS07	30	2.0	40	150	-40 to 150	0.5	0.45	2.0	130	
	CMS17	30	2.0	30	150	-40 to 150	0.1	0.48	2.0	90	
	CMS20I30A	30	2.0	30	150	-55 to 150	0.1	0.45	2.0	82	
-	CMS01 CMS03	30 30	3.0	40	125	-40 to 150	5.0	0.37	3.0	190	
			3.0	40	150	-40 to 150	0.5	0.45	3.0	190	
42	CMS30I30A CMS04	30 30	3.0 5.0	30 70	150 125	-55 to 150	8.0	0.49	3.0 5.0	82 330	VR = 10 V,
	CMS05	30	5.0	70	150	-40 to 150	0.8	0.37	5.0	330	f = 1 MHz
	CMS10	40	1.0	25	150	-40 to 150	0.6	0.45	1.0	50	
M-FLAT™	CMS10I40A	40	1.0	25	150	-55 to 150	0.5	0.35	1.0	62	
	CMS15I40A	40	1.5	25	150	-55 to 150	0.1	0.45	1.5	62	-
	CMS13140A	40	2.0	30	150	-40 to 150	0.1	0.49	2.0	95	
	CMS20I40A	40	2.0	25	150	-55 to 150	0.5	0.52	2.0	62	
	CMS16	40	3.0	30	150	-40 to 150	0.1	0.52	3.0	95	
	CMS30I40A	40	3.0	25	150	-40 to 150 -55 to 150	0.2	0.55	3.0	62	-
	CMS14	60	2.0	40	150	-40 to 150	0.1	0.58	2.0	77	
	CMS14	60	3.0	60	150	-40 to 150	0.2	0.58	3.0	102	-
	CIVISTS	00	0.0	00	130	1-40 to 150	0.0	0.50	5.0	102	

 ∇ : IRRM = 5 μ A Max (VR = 5 V) \diamondsuit : IF(DC) = 3 A

Rectification Diodes

► General-Purpose Rectifiers (for reverse-current protection)

(Ta = 25°C)

		Poekage Port Number		Absolut	e Maximum		Electrical Characteristics (Max)			
	Package	Part Number	VRRM (V)	IF(AV) (A)	IFSM (A)	T _j (°C)	T _{stg} (°C)	IRRM (μA)	V _{FM} (V)	@IFM (A)
		CRG07	400	0.7	15	175	-40 to 175	10	1.1	0.7
		CRG03	400	1.0	15	150	-40 to 150	10	1.1	0.7
	\$41	CRG09 (1)	400	1.0	15	150	-40 to 150	10	1.1	0.7
	_	CRG04	600	1.0	15	150	-40 to 150	10	1.1	1.0
	S-FLAT™	CRG05	800	1.0	15	150	-40 to 150	10	1.2	1.0
Single	***	CMC02 (2)	400	1.0	30	150	-40 to 150	10	1.0	1.0
Siu		CMG05	400	1.0	15	150	-40 to 150	10	1.1	1.0
		CMG07	400	1.0	30	150	-40 to 150	10	1.1	1.0
		CMG02	400	2.0	80	150	-40 to 150	10	1.1	2.0
		CMG06	600	1.0	15	150	-40 to 150	10	1.1	1.0
	M-FLAT™	CMG08	600	1.0	30	150	-40 to 150	10	1.1	1.0
	IVI-FLAT	CMG03	600	2.0	80	150	-40 to 150	10	1.1	2.0
Dual		HMG02 ⁽³⁾	400	0.7	10	175	-40 to 175	10	1.0	0.5
	HM-FLAT									

⁽¹⁾ High ESD protection

► Super-Fast-Recovery Diodes (S-FRDs)

 $(Ta = 25^{\circ}C)$

			Absolute	Maximum	Ratings		Electrical Characteristics (Max)				
Package	Part Number	VRRM (V)	IF(AV) (A)	IFSM (A)	T _j (°C)	T _{stg} (°C)	Irrm (μA)	VFM (V)	@ IFM (A)	trr (ns)	Conditions
-4	CRF02	800	0.5	10	150	-40 to 150	50	3.0	0.5	100	IF = 1 A,
S-FLAT™	CRF03	600	0.7	10	150	-40 to 150	50	2.0	0.7	100	di/dt = -30 A/μs
100	CMF01	600	2.0	30	150	-40 to 150	50	2.0	2.0	100	
	CMF02	600	1.0	10	150	-40 to 150	50	2.0	1.0	100	
441	CMF04	800	0.5	10	150	-40 to 150	50	2.5	0.5	100	IF = 1 A, $di/dt = -30 A/\mu s$
	CMF03	900	0.5	10	125	-40 to 150	50	2.5	0.5	100	
M-FLAT™	CMF05	1000	0.5	10	125	-40 to 150	50	2.7	0.5	100	

► High-Efficiency Diodes (HEDs)

(Ta = 25°C)

											(14 = 23 0)	
			Absolute Maximum Ratings					Electrical Characteristics (Max)				
Package	Part Number	VRRM (V)	I _{F(AV)} (A)	Ifsм (A)	T _j (°C)	T _{stg} (°C)	Irrм (μA)	VFM (V)	@ IFM (A)	trr (ns)	Conditions	
	CRH02	200	0.5	10	150	-40 to 150	10	0.95	0.5	35	IF = 1 A,	
S-FLAT™	CRH01	200	1.0	15	150	-40 to 150	10	0.98	1.0	35	di/dt = -30 A/μs	
	СМН04	200	1.0	20	150	-40 to 150	10	0.98	1.0	35		
***	СМН07	200	2.0	40	150	-40 to 150	10	0.98	2.0	35	IF = 1 A, di/dt = -30 A/μs	
M-FLAT™	CMH01	200	3.0	40	150	-40 to 150	10	0.98	3.0	35		

⁽²⁾ Designed for strobe discharge applications

⁽³⁾ IF(AV), IFSM, IRRM and VFM are specified per diode.

Product Characteristics

► SMALL & MEDIUM DIODES

Zener Diodes

► CRY/CRZ Series (S-FLAT™)

Power Dissipation: 0.7 W

 $(Ta = 25^{\circ}C)$

		Zener Characteristics						Temperature Coefficient of			Reverse	
Part Number	Power Dissipation (W)	Zei	ner Volta Vz (V)	age	Dynamic Resistance rd (Ω)	Measurement Current Iz (mA)	Zener Voltage		Voltage V _F (V)	Measurement Current IF (A)	Current IR (µA)	Measurement Voltage V _R (V)
		Min	Тур.	Max	Max	(11,7,1)	Тур.	Тур. Мах	Max	(71)	Max	(*)
CRY62	0.7	5.6	6.2	6.8	60	10	2	3	1.0	0.2	10	3.0
CRY68	0.7	6.2	6.8	7.4	60	10	3	4	1.0	0.2	10	3.0
CRY82	0.7	7.4	8.2	9.0	30	10	4	6	1.0	0.2	10	4.9
CRZ10	0.7	9.0	10.0	11.0	30	10	6	9	1.0	0.2	10	6.0
CRZ12	0.7	10.8	12.0	13.2	30	10	8	13	1.0	0.2	10	8.0
CRZ13	0.7	11.7	13.0	14.3	30	10	9	14	1.0	0.2	10	9.0
CRZ15	0.7	13.5	15.0	16.5	30	10	11	17	1.0	0.2	10	10.0
CRZ16	0.7	14.4	16.0	17.6	30	10	12	19	1.0	0.2	10	11.0
CRZ18	0.7	16.2	18.0	19.8	30	10	14	23	1.0	0.2	10	13.0
CRZ20	0.7	18.0	20.0	22.0	30	10	16	26	1.0	0.2	10	14.0
CRZ24	0.7	21.6	24.0	26.4	30	10	20	32	1.0	0.2	10	17.0
CRZ27	0.7	24.3	27.0	29.7	30	10	23	36	1.0	0.2	10	19.0
CRZ30	0.7	27.0	30.0	33.0	30	10	25	40	1.0	0.2	10	21.0
CRZ33	0.7	29.7	33.0	36.3	30	10	26	41	1.0	0.2	10	26.4
CRZ36	0.7	32.4	36.0	39.6	30	9	28	45	1.0	0.2	10	28.8
CRZ39	0.7	35.1	39.0	42.9	35	8	30	48	1.0	0.2	10	31.2

► CMZB Series (M-FLAT™)

Power Dissipation: 1 W

(Ta = 25°C)

												(1a = 25 C)	
	Power Dissipation (W)	Zener Characteristics						Temperature Coefficient of		Forward		Reverse	
Part Number		Zener Voltage Vz (V)			Dynamic Resistance rd (Ω)	Iz	Zener Voltage ατ (mV/°C)		Voltage V _F (V)	Measurement Current	Current I _R (μA)	Measurement Voltage VR	
		Min	Тур.	Max	Max	(mA)	Тур.	Max	Max	(A)	Max	(V)	
CMZB12	1.0	10.8	12	13.2	30	10	8	13	1.2	0.2	10	8	
CMZB13	1.0	11.7	13	14.3	30	10	9	14	1.2	0.2	10	9	
CMZB15	1.0	13.5	15	16.5	30	10	11	17	1.2	0.2	10	10	
CMZB18	1.0	16.2	18	19.8	30	10	14	23	1.2	0.2	10	13	
CMZB20	1.0	18.0	20	22.0	30	10	16	26	1.2	0.2	10	14	
CMZB24	1.0	21.6	24	26.4	30	10	20	32	1.2	0.2	10	17	
CMZB27	1.0	24.3	27	29.7	30	10	23	36	1.2	0.2	10	19	
CMZB30	1.0	27.0	30	33.0	30	10	25	40	1.2	0.2	10	21	
CMZB33	1.0	29.7	33	36.3	30	10	26	41	1.2	0.2	10	26.4	
CMZB36	1.0	32.4	36	39.6	30	9	28	45	1.2	0.2	10	28.8	
CMZB39	1.0	35.1	39	42.9	35	8	30	48	1.2	0.2	10	31.2	
CMZB43	1.0	38.7	43	47.3	40	7	33	53	1.2	0.2	10	34.4	
CMZB47	1.0	42.3	47	51.7	65	6	38	60	1.2	0.2	10	37.6	
CMZB51	1.0	45.9	51	56.1	65	6	43	68	1.2	0.2	10	40.8	
CMZB68	1.0	61.2	68	74.8	120	4	57	90	1.2	0.2	10	54.4	
CMZB75	1.0	67.5	75	82.5	150	4	66	104	1.2	0.2	10	60	
CMZB82	1.0	73.8	82	90.2	170	3	71	113	1.2	0.2	10	65.6	

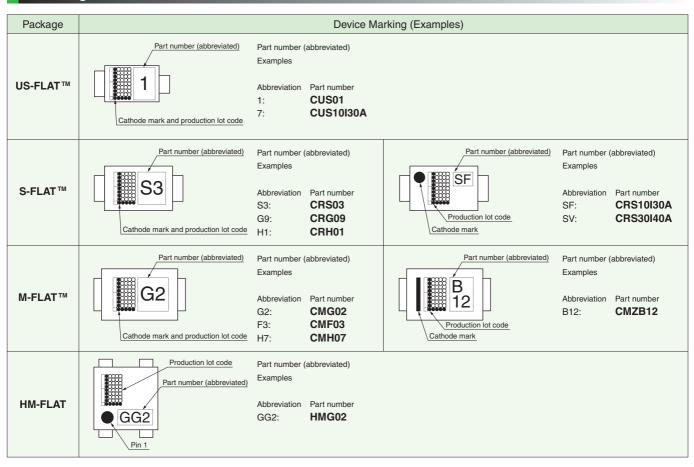
► CMZ Series (M-FLAT™)

Power Dissipation: 2 W

 $(Ta = 25^{\circ}C)$

Part Number	Power Dissipation (W)	$\begin{array}{ c c c c c }\hline & Zenier \ Voltage \\ \hline & Vz \ (V) \\ \hline & rd \ (\Omega) \\ \hline & Iz \\ \hline \end{array}$					Temperature Coefficient of Zener Voltage		Forward Voltage VF (V) Measurement Current IF (A)		Reverse Current IR (µA) Measurement Voltage VR (V)	
		Min	Тур.	Max	Max	(11174)	Тур.	Max	Max	(71)	Max	(-)
CMZ12	2.0	10.8	12	13.2	30	10	8	13	1.2	0.2	10	8
CMZ13	2.0	11.7	13	14.3	30	10	9	14	1.2	0.2	10	9
CMZ15	2.0	13.5	15	16.5	30	10	11	17	1.2	0.2	10	10
CMZ18	2.0	16.2	18	19.8	30	10	14	23	1.2	0.2	10	13
CMZ20	2.0	18.0	20	22.0	30	10	16	26	1.2	0.2	10	14
CMZ24	2.0	21.6	24	26.4	30	10	20	32	1.2	0.2	10	17
CMZ27	2.0	24.3	27	29.7	30	10	23	36	1.2	0.2	10	19
CMZ30	2.0	27.0	30	33.0	30	10	25	40	1.2	0.2	10	21
CMZ33	2.0	29.7	33	36.3	30	10	26	41	1.2	0.2	10	26.4
CMZ36	2.0	32.4	36	39.6	30	9	28	45	1.2	0.2	10	28.8
CMZ39	2.0	35.1	39	42.9	35	8	30	48	1.2	0.2	10	31.2
CMZ43	2.0	38.7	43	47.3	40	7	33	53	1.2	0.2	10	34.4
CMZ47	2.0	42.3	47	51.7	65	6	38	60	1.2	0.2	10	37.6
CMZ51	2.0	45.9	51	56.1	65	6	43	68	1.2	0.2	10	40.8

Marking



Note

Note

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